

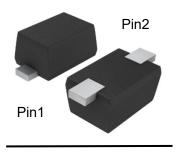


ESD Protector

Description

The PESDNC5D12VB ESD protector is designed to replace multilayer varistors (MLVs) in portable applications such as cell phones, notebook computers, and PDAs. They feature large cross-sectional area junctions for conducting high transient currents, offer desirable electrical characteristics for board level protection, such as fast response time, lower operating voltage, lower clamping voltage and no device degradation when compared to MLVs.

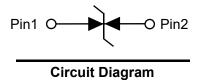
The PESDNC5D12VB protects sensitive semiconductor components from damage or upset due to electrostatic discharge (ESD) and other voltage induced transient events. It gives designer the flexibility to protect one unidirectional line in applications where arrays are not practical.



SOD-523

Feature

- \gt 120W peak pulse power per line (t_P = 8/20µs)
- ➤ SOD-523 package
- > Replacement for MLV(0603)
- > Response time is typically < 1 ns
- > Protect one I/O or power line
- > Low clamping voltage
- > RoHS compliant
- Transient protection for data lines to IEC 61000-4-2(ESD) ±30KV(air), ±30KV(contact);



Applications

- > Cell phone handsets and accessories
- Personal digital assistants (PDAs)
- Notebooks, desktops, and servers
- Digital cameras
- > Peripherals
- ➤ MP3 players

Pin1 AC Pin2 Marking (Top View)

Mechanical Characteristics

➤ Lead finish:100% matte Sn(Tin)

Mounting position: Any

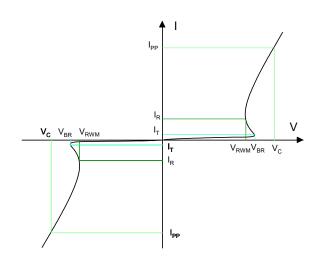
➤ Qualified max reflow temperature:260°C

➤ Pure tin plating: 7 ~ 17 um

➤ Pin flatness:≤3mil

Electronics Parameter

Symbol	Parameter		
V_{RWM}	Peak Reverse Working Voltage		
I _R	Reverse Leakage Current @ V _{RWM}		
V_{BR}	Breakdown Voltage @ I _T		
I _T	Test Current		
I _{PP}	Maximum Reverse Peak Pulse Current		
V _C	Clamping Voltage @ I _{PP}		
P _{PP}	Peak Pulse Power		
CJ	Junction Capacitance		
I _F	Forward Current		
V _F	Forward Voltage @ I _F		



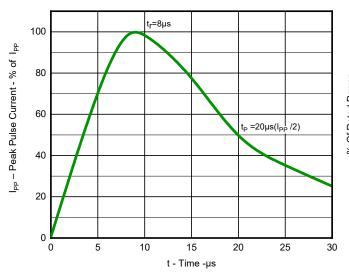
Electrical characteristics per line@25°C (unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Units
Peak Reverse Working Voltage	V_{RWM}	-	-	-	12	V
Breakdown Voltage	V_{BR}	I _t = 1mA	12.3	1	1	V
Reverse Leakage Current	I _R	V _{RWM} = 12V	-	-	1.0	μA
Clarania a Valta a	V _{CL}	TLP = 4A, $t_p = 100 \text{ns}$	-	13	-	V
Clamping Voltage		TLP = 16A, $t_p = 100 \text{ns}$	-	14.5	-	
Clamping Voltage	V _C	$I_{PP} = 7A, t_P = 8/20 \mu s$	-	18	20	V
Junction Capacitance	CJ	$V_R = 0V, f = 1MHz$	-	7.0	-	pF

Absolute maximum rating@25°C

Rating	Symbol	Value	Units
Peak Pulse Power (t _P = 8/20µs)	P _{PP}	120	W
Peak Pulse Current (t _P = 8/20μs)	I _{PP}	7.0	А
Lead Soldering Temperature	T _L	260 (10 sec)	°C
Junction and Storage Temperature Range	$T_{J,}T_{STG}$	-55~+150	°C
ESD Protection-Contact Discharge	V _{ESD}	±30	kV
ESD Protection-Air Discharge	V _{ESD}	±30	kV

Typical Characteristics



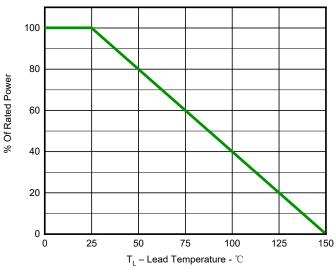


Fig 1.Pulse Waveform(8/20µs)

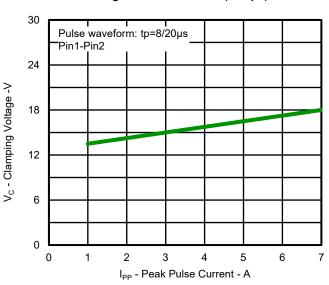


Fig 2.Power Derating Curve

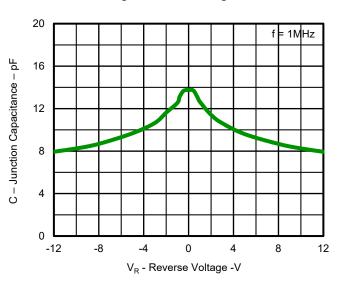


Fig.3 Clamping Voltage vs. Peak Pulse Current

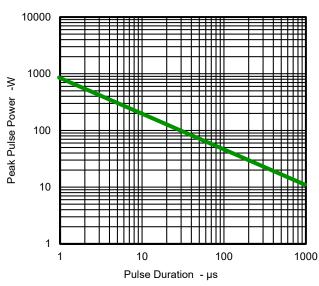


Fig.4 Capacitance vs. Reveres Voltage

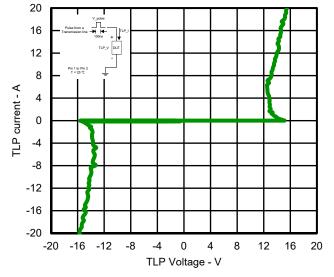
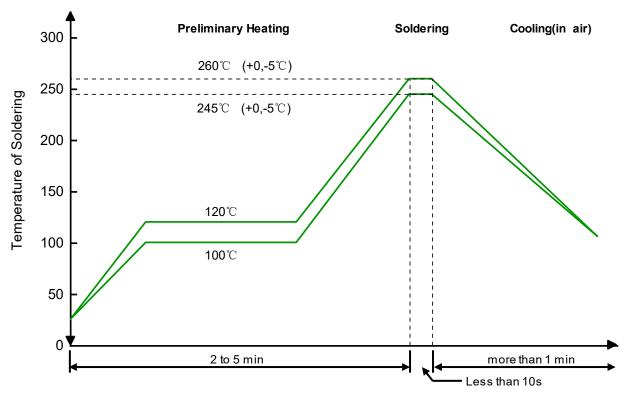


Fig.5 Non-Repetitive Peak Pulse Power vs. Pulse Time

Fig.6 TLP Measurement

Solder Reflow Recommendation



Remark: Pb free for 260°C; Pb for 245°C.

PCB Design

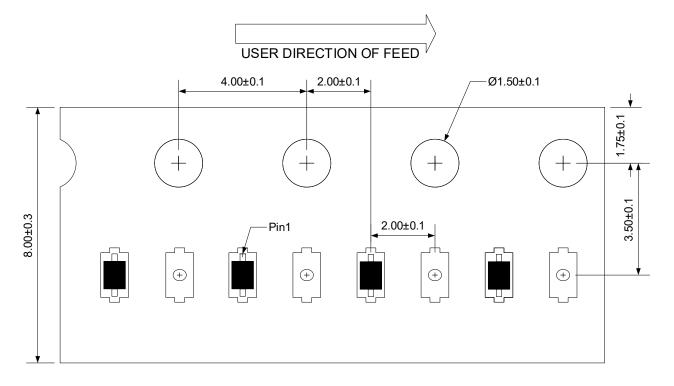
For TVS diodes a low-ohmic and low-inductive path to chassis earth is absolutely mandatory in order to achieve good ESD protection. Novices in the area of ESD protection should take following suggestions to heart:

- > Do not use stubs, but place the cathode of the TVS diode directly on the signal trace.
- > Do not make false economies and save copper for the ground connection.
- > Place via holes to ground as close as possible to the anode of the TVS diode.
- Use as many via holes as possible for the ground connection.
- > Keep the length of via holes in mind! The longer the more inductance they will have.

Ordering information

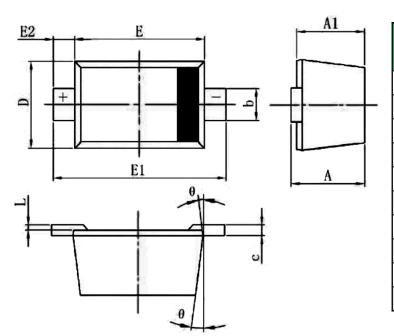
Package	Reel	Shipping
SOD-523	7"	3000 / Tape & Reel

Load with information

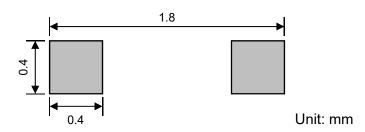


Unit:mm

Product Dimension (SOD-523)



Dim	Millimeters		Inches		
	Min	Max	Min	Max	
Α	0.41	0.77	0.016	0.030	
A1	0.40	0.70	0.016	0.028	
b	0.25	0.35	0.010	0.014	
С	0.07	0.20	0.003	0.008	
D	0.70	0.90	0.028	0.035	
Е	1.10	1.30	0.043	0.051	
E1	1.50	1.70	0.059	0.067	
E2	0.20 Ref.		0.008	Ref.	
L	0.01	0.07	0.000	0.003	
θ	7°		7	' 0	



Suggested PCB Layout

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